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for Power Electronics, Intelligent Motion,
Renewable Energy and Energy Management

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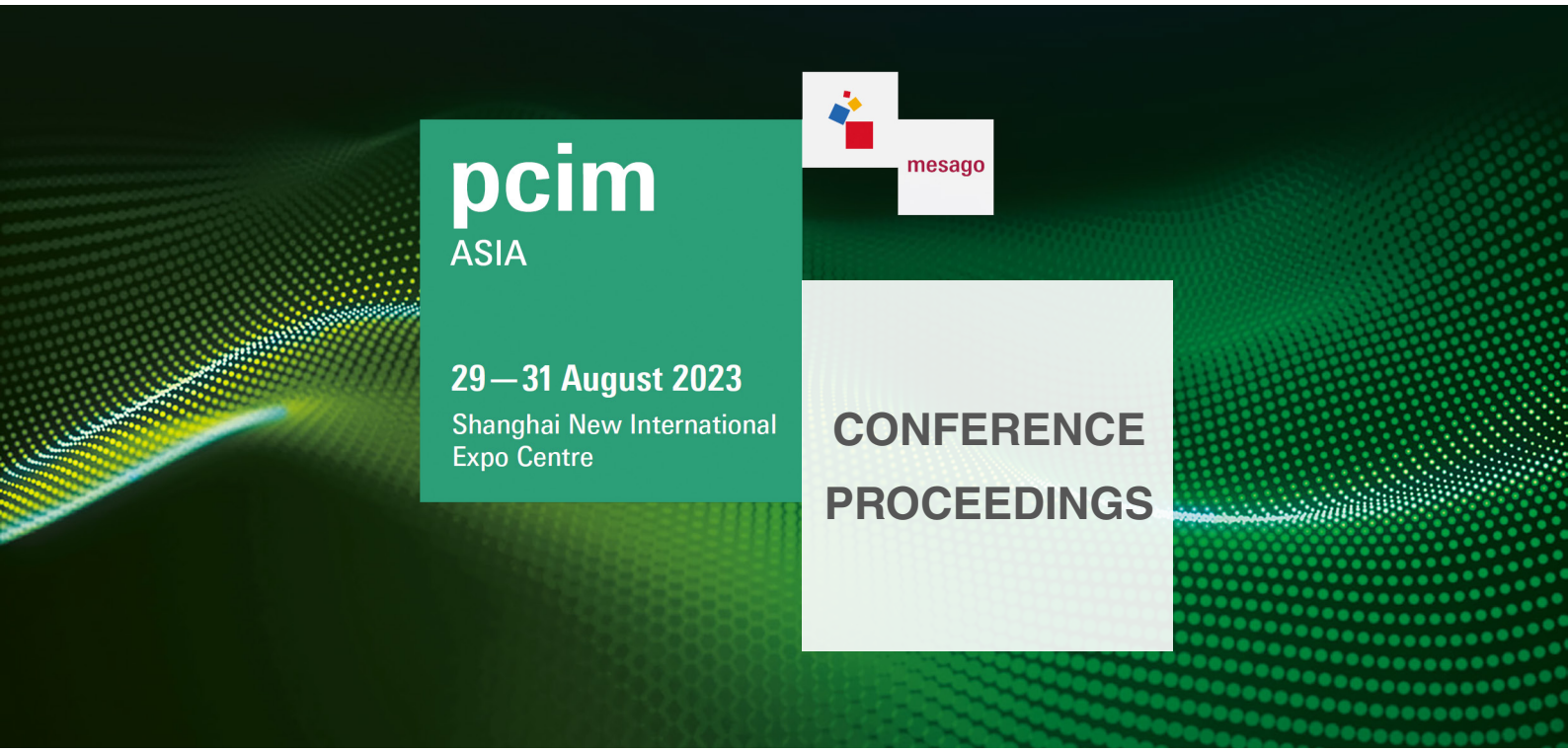

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PCIM Asia 2023 Conference Welcome Address

Dear PCIM Asia participants,

I am very happy and proud to welcome all of you to the PCIM Asia Conference and Exhibition 2023 in Shanghai.

The PCIM Asia Conference brings together the world´s foremost experts and decision maker from industry and academia in the field of power electronic components and systems to discuss future technology trends and launching new products in the market. Power electronic components and energy conversion systems today are driven by WBG technologies, the electrification of all transportation vehicles, renewable energy technologies, communication equipment and artificial intelligence. WBG devices gives a new freedom in the design of ultra-high power density converters along with high efficiency ratings. Researchers from academia and experts from industry will provide presentations covering new developments in the field of power devices, advanced packaging technologies with outstanding reliability, future power converters for automotive and renewable energy systems. This year in our technical program we are covering innovations along the power electronic roadmap in addition to three leading experts for keynote presentations, one special session on GaN based high power density supplies and one tutorial on advanced power modules. The PCIM Asia is a worldwide magnet for design engineers and researchers in the field of power electronics as well as decision makers from companies to generate new market segments and trigger future research directions.

Important innovations on components and system level will be outlined during this year´s PCIM Asia Conference

The technical program of this year´s PCIM Asia is covering new development achievements on power semiconductor devices based on Si and WBG technologies including relevant packaging designs handling ultrafast switching devices with extended lifetime and sensing parameters for predictive diagnostic functions as well as smart digital controlled power conversion concepts for traction and grid applications.

Conference highlights and future milestones in the value-added chain of power electronics

The keynote presentations on the new generation of GaN power devices, packaging designs for high power density and high voltage capabilities as well as dedicated high voltage semiconductor switches for wind power applications together with GaN based ultra-high power density power supplies will attract many power electronics experts.

Special attention has been paid to research carried out by engineers from industries and universities with their presentations and “Best Paper Award”, “Young Engineer Award” and “University Scientist Award” during the PCIM Asia conference 2023 – these are certainly further highlights of the conference.

I wish you an enjoyable and successful conference, an open dialog with all the experts and packed with new ideas for your future product innovation and business.

Leo Lorenz

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